

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

**PRELIMINARY AMENDMENT ACCOMPANYING APPLICATION**

APPLICANT: Fumihiko Nakamura, et al. ATTY. DOCKET NO. 09792909-5122

SERIAL NO.

DATE FILED:

INVENTION: "INSULATING NITRIDE LAYER AND PROCESS FOR ITS FORMING,  
AND SEMICONDUCTOR DEVICE AND PROCESS FOR ITS  
PRODUCTION"

Assistant Commissioner of Patents  
Washington, D.C. 20231


S I R:

Between the title and the heading "Background of the Invention" on page 1, insert the  
following:

--RELATED APPLICATION DATA

The present application claims priority to Japanese Application No. P2000-241581 filed  
August 9, 2000, which application is incorporated herein by reference to the extent permitted by  
law.--

Respectfully submitted,

 (Reg. No. 32,919)  
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